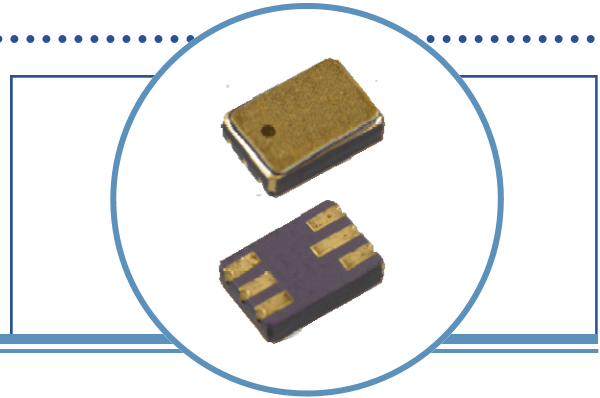


Surface Mount Optically Coupled Isolator JAN / JANTX / JANTXV 4N47U, 4N48U, 4N49U



Features:

- Surface Mount (SM), Leadless Chip Carrier (LCC)
- 1 kV electrical isolation
- Base contact provided for conventional transistor biasing
- JANTX and JANTXV devices are processed to MIL-PRF-19500



Description:

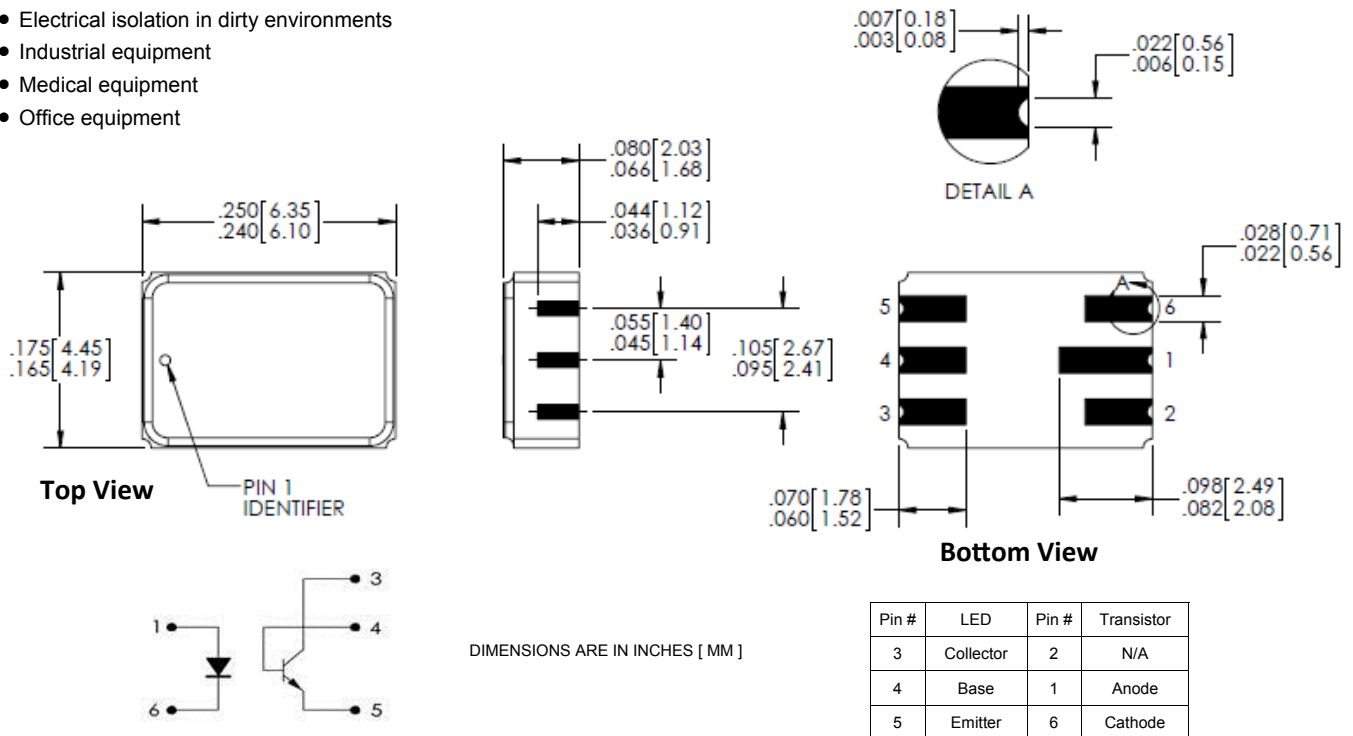
Each isolator in this series consists of an infrared emitting diode and a NPN silicon phototransistor, which are mounted in a hermetically sealed Surface Mount, 6 Pin package. Devices are designed for military and/or harsh environments.

The JAN / JANTX / JANTXV 4N47U, 4N48U and 4N49U devices are processed to MIL-PRF-19500/548. This series of 4N products are JEDEC registered, DSCC qualified.

Please contact your local representative or OPTEK for more information.

Applications:

- Military equipment
- High-Reliability environments
- High voltage isolation between input and output
- Electrical isolation in dirty environments
- Industrial equipment
- Medical equipment
- Office equipment



This product is built, tested and shipped from the USA



OPTEK reserves the right to make changes at any time in order to improve design and to supply the best product possible.

Surface Mount Optically Coupled Isolator

JAN / JANTX / JANTXV 4N47U, 4N48U, 4N49U



Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Storage Temperature Range	-55° C to +150° C
Operating Temperature Range	-55° C to +125° C
Input-to-Output Isolation Voltage	$\pm 1.00\text{ kVDC}^{(1)}$
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 seconds with soldering iron]	260° C ⁽²⁾

Input Diode

Forward DC Current (65° C or below)	40 mA
Reverse Voltage	2 V
Power Dissipation	60 mW ⁽³⁾

Output Phototransistor:

Continuous Collector Current	50 mA
Collector-Emitter Voltage	40 V
Collector-Base Voltage	45 V
Emitter-Base Voltage	7.0 V
Power Dissipation	300 mW ⁽⁴⁾

Notes:

1. Measured with input leads shorted together and output leads shorted together.
2. RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.
3. Derate linearly 1.0 mW/° C above 65° C.
4. Derate linearly 3.0 mW/° C above 25° C.

Ordering Information				
Part Number	Isolation Voltage (kV)	I _F (mA) Typ / Max	V _{CE} (Volts) Max	Processing MIL-PRF-195000
JAN4N47U	1	1 / 40	40	548
JANTX4N47U				
JANTXV4N47U				
JAN4N48U				
JANTX4N48U				
JANTXV4N48U				
JAN4N49U				
JANTX4N49U				
JANTXV4N49U				

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Surface Mount Optically Coupled Isolator

JAN / JANTX / JANTXV 4N47U, 4N48U, 4N49U



Electrical Characteristics (T_A = 25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
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Input Diode

V _F	Forward Voltage	0.80 1.00 0.70	- - -	1.50 1.70 1.30	V	I _F = 10.0 mA I _F = 10.0 mA, T _A = -55° C ⁽¹⁾ I _F = 10.0 mA, T _A = 100° C ⁽¹⁾
I _R	Reverse Current	-	-	100	µA	V _R = 2.0 V

Output Phototransistor

V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	40	-	-	V	I _C = 1.0 mA, I _B = 0, I _F = 0
V _{(BR)CBO}	Collector-Base Breakdown Voltage	45	-	-	V	I _C = 100 µA, I _B = 0, I _F = 0
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	7	-	-	V	I _E = 100 µA, I _C = 0, I _F = 0
I _{C(OFF)} ¹	Collector-Emitter Dark Current	-	-	100	nA	V _{CE} = 20 V, I _B = 0, I _F = 0
I _{C(OFF)} ²	Collector-Emitter Dark Current	-	-	100	µA	V _{CE} = 20 V, I _B = 0, I _F = 0, T _A = 100° C ⁽¹⁾
I _{CB(OFF)}	Collector-Base Dark Current	-	-	10	nA	V _{CB} = 20 V, I _E = 0, I _F = 0

Coupled

I _{C(ON)}	On-State Collector Current JAN / JANTX / JANTXV 4N47 [U]	0.50 0.70 0.50	- - -	- - -	mA	I _F = 1.0 mA, V _{CE} = 5.0 V, I _B = 0 I _F = 2.0 mA, V _{CE} = 5.0 V, I _B = 0, T _A = -55° C ⁽¹⁾ I _F = 2.0 mA, V _{CE} = 5.0 V, I _B = 0, T _A = 100° C ⁽¹⁾
	JAN / JANTX / JANTXV 4N48 [U]	1.00 1.40 1.00	- - -	5 - -		I _F = 1.0 mA, V _{CE} = 5.0 V, I _B = 0 I _F = 2.0 mA, V _{CE} = 5.0 V, I _B = 0, T _A = -55° C ⁽¹⁾ I _F = 2.0 mA, V _{CE} = 5.0 V, I _B = 0, T _A = 100° C ⁽¹⁾
	JAN / JANTX / JANTXV 4N49 [U]	2.00 2.80 2.00	- - -	10 - -		I _F = 1.0 mA, V _{CE} = 5.0 V, I _B = 0 I _F = 2.0 mA, V _{CE} = 5.0 V, I _B = 0, T _A = -55° C ⁽¹⁾ I _F = 2.0 mA, V _{CE} = 5.0 V, I _B = 0, T _A = 100° C ⁽¹⁾
I _{CB(ON)}	On-State Collector Base	30	-	-	µA	V _{CB} = 5 V, I _E = 0, I _F = 10 mA
V _{CE(SAT)}	Collector-Emitter Saturation Voltage JAN / JANTX / JANTXV 4N47 [U]	-	-	0.30	V	I _F = 2.0 mA, I _C = 0.5 mA, I _B = 0
	JAN / JANTX / JANTXV 4N48 [U]	-	-	0.30		I _F = 2.0 mA, I _C = 1.0 mA, I _B = 0
	JAN / JANTX / JANTXV 4N49 [U]	-	-	0.30		I _F = 2.0 mA, I _C = 2.0 mA, I _B = 0
H _{FE}	DC Current Gain	100	-	-	V	V _{CE} = 5.0 V, I _C = 10.0 mA, I _F = 0 mA
R _{IO}	Resistance (Input-to-Output)	10 ¹¹	-	-	Ω	V _{I-O} = ± 1000 VDC ⁽³⁾
C _{IO}	Capacitance (Input-to-Output)	-	-	5	pF	V _{I-O} = 0 V, f = 1.0 MHz ⁽³⁾
T _R , T _F	Rise and Fall Time	-	-	20	µs	V _{CC} = 10.0 V, I _F = 5.0 mA, R _L = 100 Ω

Notes:

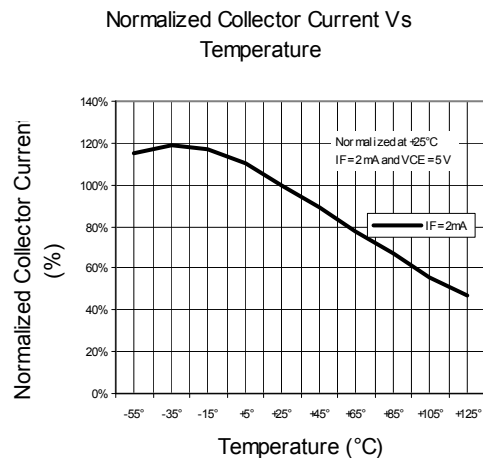
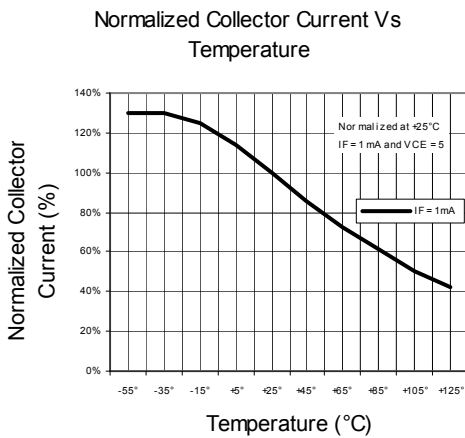
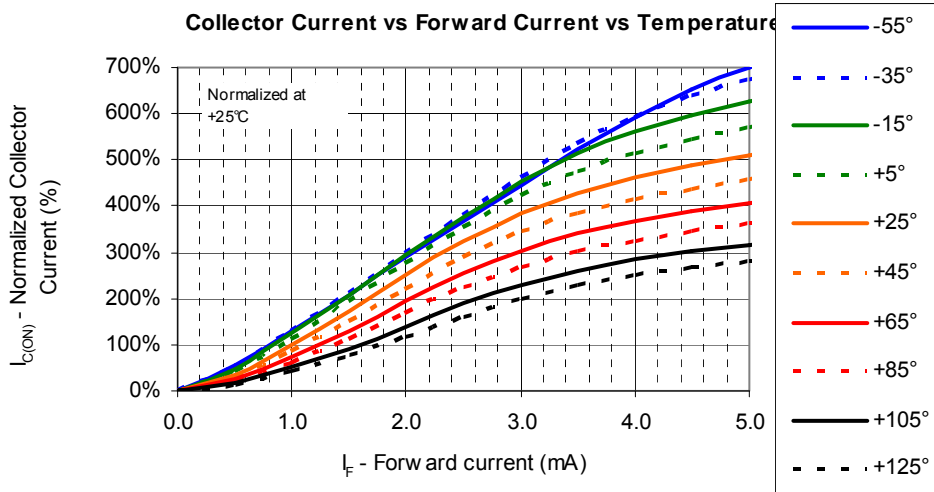
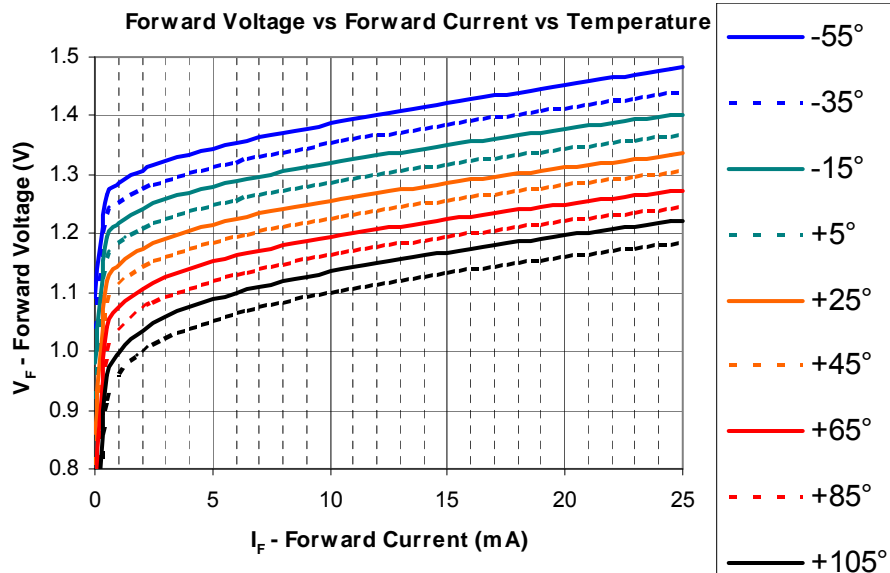
1. Guaranteed but not tested.
2. Sample tested, LTPD = 10.
3. Measured with input leads shorted together and output leads shorted together.

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Typical Performance Curves



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